

## WIDEBAND, LOW-NOISE, LOW DISTORTION, FULLY DIFFERENTIAL AMPLIFIER

#### **FEATURES**

- **Fully Differential Architecture**
- **Centered Input Common-Mode Range**

**UMENTS** 

- Minimum Gain of 1 V/V (0 dB)
- Bandwidth: 1600 MHz Slew Rate: 5100 V/µs
- 1% Settling Time: 2.9 ns HD<sub>2</sub>: -75 dBc at 70 MHz
- HD<sub>3</sub>: -86 dBc at 70 MHz
- OIP<sub>2</sub>: 77 dBm at 70 MHz OIP<sub>3</sub>: 42 dBm at 70 MHz
- Input Voltage Noise: 2.2 nV/√Hz (f > 10 MHz)
- Noise Figure: 19.8 dB
- **Output Common-Mode Control**
- **Power Supply:** 
  - Voltage: 3 V (±1.5 V) to 5 V (±2.5 V)
  - Current: 37.7 mA
- Power-Down Capability: 0.65 mA

#### **APPLICATIONS**

- 5-V Data Acquisition Systems, High Linearity **ADC Amplifier**
- **Wireless Communication**
- **Medical Imaging**
- **Test and Measurement**

#### RELATED PRODUCTS

Device	Min. Gain	Common-Mode Range of Input <sup>(1)</sup>
THS4508	6 dB	-0.3 V to 2.3 V
THS4509	6 dB	1.1 V to 3.9 V
THS4511	0 dB	-0.3 V to 2.3 V
THS4513	0 dB	1.1 V to 3.9 V

1. Assumes a 5-V single-ended power supply.

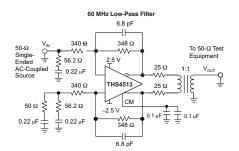
#### DESCRIPTION

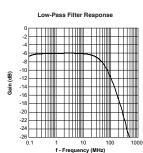
The THS4513 is a wideband, fully differential op amp designed for 3.3 V to 5 V data acquisition systems. It has very low noise at 2.2 nV/ $\sqrt{\text{Hz}}$ , and extremely low harmonic distortion of -75 dBc HD<sub>2</sub> and -86 dBc HD<sub>3</sub> at 70 MHz with 2-V<sub>PP</sub> output, G = 0 dB, and 200- $\Omega$  load. Slew rate is very high at 5100 V/ $\mu$ s and with settling time of 2.9 ns to 1% (2 V step), it is ideal for pulsed applications. It is designed for a minimum gain of 0 dB.

To allow for dc-coupling to ADCs, its unique output common-mode control circuit maintains the output common-mode voltage within 5 mV offset (typ) from the set voltage, when set within 0.5 V of mid-supply, with less than 4 mV differential offset voltage. The common-mode set point is set to mid-supply by internal circuitry, which may be over-driven from an external source.

The input and output are optimized for best performance with their common-mode voltages set to mid-supply. Along with high performance at low power-supply voltage, this design makes it ideal for extremely high-performance, single-supply 5 V data acquisition systems.

The THS4513 is offered in a quad, leadless QFN-16 package (RGT), and is characterized for operation over the full industrial temperature range from -40°C to +85°C.





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This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### PACKAGING/ORDERING INFORMATION(1)

	PACKAGE	D DEVICES
TEMPERATURE	QUAD QFN <sup>(2) (3)</sup> (RGT-16)	SYMBOL
-40°C to +85°C	THS4513RGTT	
-40°C (0 +65°C	THS4513RGTR	_

- (1) For the most current package and ordering information see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.
- (2) This package is available taped and reeled. The R suffix standard quantity is 3000. The T suffix standard quantity is 250.
- (3) The exposed thermal pad is electrically isolated from all other pins.

#### **ABSOLUTE MAXIMUM RATINGS**(1)

Over operating free-air temperature range, unless otherwise noted.

			UNIT
V <sub>S</sub> - to V <sub>S</sub> +	Supply voltage		6 V
V <sub>I</sub>	Input voltage		±V <sub>S</sub>
V <sub>ID</sub>	Differential input	t voltage	4 V
Io	Output current (2		200 mA
	Continuous pow	er dissipation	See Dissipation Rating Table
T <sub>J</sub>	Maximum junction	on temperature	+150°C
T <sub>A</sub>	Operating free-a	air temperature range	-40°C to +85°C
T <sub>stg</sub>	Storage tempera	ature range	−65°C to +150°C
	Lead temperatur	re 1,6 mm (1/16 inch) from case for 10 seconds	+300°C
		НВМ	2000 V
	ESD ratings	CDM	1500 V
		MM	100 V

- (1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.
- (2) The THS4513 incorporates a (QFN) exposed thermal pad on the underside of the chip. This pad acts as a heatsink and must be connected to a thermally dissipative plane for proper power dissipation. Failure to do so may result in exceeding the maximum junction temperature which could permanently damage the device. See TI technical briefs SLMA002 and SLMA004 for more information about utilizing the QFN thermally-enhanced package.

#### **DISSIPATION RATINGS TABLE**

PACKAGE	Δ	Δ	POWER RATING	
FACKAGE	A1C	⊎JA	T <sub>A</sub> ≤ +25°C	$T_A = +85^{\circ}C$
RGT (16)	2.4°C/W	39.5°C/W	2.3 W	225 mW

Product Folder Link(s): THS4513

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## ELECTRICAL CHARACTERISTICS: $V_{S+} - V_{S-} = 5 \text{ V}$

Test conditions at  $V_{S+}=2.5$  V,  $V_{S-}=-2.5$  V, G=0 dB, CM= open,  $V_{O}=2$   $V_{PP}$ ,  $R_{F}=348$   $\Omega$ ,  $R_{L}=200$   $\Omega$  differential,  $T_{A}=+25^{\circ}C$ , single-ended input, differential output, and input and output referenced to mid-supply, unless otherwise noted.

PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT	TEST LEVEL <sup>(1)</sup>
AC PERFORMANCE			"		· ·		Ш
0 11 1 11 11	$G = 0 \text{ dB}, V_O = 100 \text{ mV}_{PF}$	<b>.</b>		1.6		GHz	
Small-signal bandwidth	$G = 6 \text{ dB}, V_O = 100 \text{ mV}_{PF}$	$3 = 6 \text{ dB}, V_0 = 100 \text{ mV}_{PP}$		1.4		GHz	
Gain-bandwidth product	G = 6 dB			2.8		GHz	
D 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	$G = 0 \text{ dB}, V_O = 2 V_{PP}$			150			1
Bandwidth for 0-dB flatness	$G = 6 dB, V_O = 2 V_{PP}$			700		MHz	
Large-signal bandwidth	$G = 0 dB, V_O = 2 V_{PP}$			1.4		GHz	
Slew rate (differential)				5100		V/μs	
Disc time fall time				0.5			
Rise time fall time	2-V Step			0.5		no	
Settling time to 1%				2.9		ns	
Settling time to 0.1%				16			
	f = 10 MHz			-110			
2nd-order harmonic distortion	f = 50 MHz			-80		dBc	
	f = 100 MHz			-66			
3rd-order harmonic distortion	f = 10 MHz			-108		dBc	
	f = 50 MHz			-94			С
	f = 100 MHz			-81			
2nd-order intermodulation distortion		f <sub>C</sub> = 70 MHz		-78		- dBc	
2nd-order intermodulation distortion	V <sub>O</sub> = 2 V <sub>PP</sub> Envelope,	f <sub>C</sub> = 140 MHz		-55			
3rd-order intermodulation distortion	$=$ 200 kHz tone spacing, $R_L = 100 Ω$	f <sub>C</sub> = 70 MHz		-88			
		f <sub>C</sub> = 140 MHz		-72			
2nd order output intercent point		f <sub>C</sub> = 70 MHz		77		- dBm	
2nd-order output intercept point	200 kHz Tone spacing $R_L = 100 \Omega$	f <sub>C</sub> = 140 MHz		53			
2rd order output intercent point		$f_C = 70 \text{ MHz}$		42			
3rd-order output intercept point		f <sub>C</sub> = 140 MHz		34			
1-dB compression point	f <sub>C</sub> = 70 MHz			12.2		dD.m	
	f <sub>C</sub> = 140 MHz			10.8		dBm	
Noise figure	50 Ω System, 10 MHz, G	= 6 dB		19.8		dB	
Input voltage noise	f > 10 MHz			2.2		nV/√ <del>Hz</del>	
Input current noise	f > 10 MHz			1.7		pA/√ <del>Hz</del>	
DC PERFORMANCE							
Open-loop voltage gain (A <sub>OL</sub> )				63		dB	С
Input offact voltage	T <sub>A</sub> = +25°C			1	4	mV	^
Input offset voltage	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			1	5	mV	A
Average offset voltage drift	$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$			2.6		μV/°C	В
Input bias current	T <sub>A</sub> = +25°C			8	15.5	^	^
input bias current	$T_A = -40^{\circ}C$ to $+85^{\circ}C$			8	18.5	μΑ	Α
Average bias current drift	$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$			20		nA/°C	В
Input offeet current	T <sub>A</sub> = +25°C			1.6	3.6		۸
Input offset current	$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$			1.6	7	μΑ	Α
Average offset current drift	$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$			4		nA/°C	В

<sup>(1)</sup> Test levels: (A) 100% tested at +25°C. Over-temperature limits by characterization and simulation. (B) Limits set by characterization and simulation. (C) Typical value only for information.

Product Folder Link(s): THS4513



Test conditions at  $V_{S+}=2.5$  V,  $V_{S-}=-2.5$  V, G=0 dB, CM= open,  $V_{O}=2$   $V_{PP}$ ,  $R_{F}=348$   $\Omega$ ,  $R_{L}=200$   $\Omega$  differential,  $T_{A}=+25^{\circ}C$ , single-ended input, differential output, and input and output referenced to mid-supply, unless otherwise noted.

PARAMETER	TEST COM	TEST CONDITIONS		TYP	MAX	UNIT	TEST LEVEL <sup>(1)</sup>
INPUT							
Common-mode input range high				1.4		V	
Common-mode input range low				-1.4		V	В
Common-mode rejection ratio				90		dB	
Differential input impedance				1.3    1.8		MΩ    pF	С
Common-mode input impedance				1.0    2.3		IVIZZ    PI	
OUTPUT							
Maximum output voltago high		T <sub>A</sub> = +25°C	1.2	1.4		V	
Maximum output voltage high	Each output with 100 Ω	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	1.1	1.4		V	
Minimum output valtage low	to mid-supply	T <sub>A</sub> = +25°C		-1.4	-1.2	V	Α
Minimum output voltage low		$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$		-1.4	-1.1	V	
Differential output voltage swing	T <sub>A</sub> = +25°C		4.8	5.6		V	
	$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$		4.4	5.6		V	
Differential output current drive	R <sub>L</sub> = 10 Ω			96		mA	
Output balance error	V <sub>O</sub> = 100 mV, f = 1 MHz			-52		dB	С
Closed-loop output impedance	f = 1 MHz			0.3		Ω	İ
OUTPUT COMMON-MODE VOLTAG	E CONTROL		"	<u>'</u>			"
Small-signal bandwidth			250			MHz	
Slew rate				110		V/μs	
Gain				1		V/V	
Output common-mode offset from CM input	-1 V < CM < 1 V			5		mV	С
CM input bias current	-1 V < CM < 1 V	-1 V < CM < 1 V		±40		μΑ	
CM input voltage range				-1.5 to 1.5		V	
CM input impedance				23    1		kΩ    pF	
CM default voltage				0		V	
POWER SUPPLY			"	<u>'</u>			
Specified operating voltage			3	5	5.5	V	С
NAi	T <sub>A</sub> = +25°C			37.7	40.9	A	
Maximum quiescent current	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			37.7	41.9	mA	
	T <sub>A</sub> = +25°C		34.5	37.7			A
Minimum quiescent current	$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$			37.7		mA	
Power-supply rejection (±PSRR)				90		dB	С
POWER-DOWN							
Enable voltage threshold	Referenced to V <sub>S-</sub> , Assur	ed <i>on</i> above 2.1 V + V <sub>S-</sub>		> 2.1 + V <sub>S-</sub>		V	С
Disable voltage threshold	Assured off below 0.7 V +	Assured off below 0.7 V + V <sub>S</sub> _		< 0.7 + V <sub>S-</sub>		V	
Down down guiseagnt gurrent	T <sub>A</sub> = +25°C			0.65	0.9	A	^
Power-down quiescent current	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			0.65	1	mA	Α
Input bias current	PD = V <sub>S-</sub>			100		μΑ	
Input impedance				50    2		kΩ    pF	
Turn-on time delay	Measured to output on			55		ns	С
Turn-off time delay	Measured to output off			10		μs	1

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## ELECTRICAL CHARACTERISTICS: $V_{S+} - V_{S-} = 3 \text{ V}$

Test conditions at  $V_{S+}=1.5$  V,  $V_{S-}=-1.5$  V, G=0 dB, CM= open,  $V_{O}=1$   $V_{PP}$ ,  $R_{F}=348$   $\Omega$ ,  $R_{L}=200$   $\Omega$  differential,  $T_{A}=+25^{\circ}C$ , single-ended input, differential output, and input and output referenced to mid-supply, unless otherwise noted.

PARAMETER	TEST C	ONDITIONS	ТҮР	UNIT	TEST LEVEL <sup>(1)</sup>
AC PERFORMANCE					
Small-signal bandwidth	$G = 0 dB, V_O = 100 mV_{PP}$		1.6	GHz	
Oman digital barrawan	$G = 6 \text{ dB}, V_O = 100 \text{ mV}_{PP}$		1.3	GHz	
Gain-bandwidth product	G = 6 dB		2.6	GHz	
Bandwidth for 0-dB Flatness	$G = 0 dB$ , $V_O = 1 V_{PP}$		135	MHz	
Dandwidth for 0-db Flattless	$G = 6 dB$ , $V_O = 1 V_{PP}$		450	IVII IZ	
Large-signal bandwidth	$G = 10 dB, V_O = 1 V_{PP}$		1.4	GHz	
Slew rate (differential)			2700	V/μs	
Rise time		0.25			
Fall time	1-V Step	0.25	ns		
Settling time to 1%			2.9	110	
Settling time to 0.1%					
	f = 10 MHz		-116		
2nd-order harmonic distortion	f = 50 MHz		-86	dBc	
	f = 100 MHz		-60		
	f = 10 MHz		-83		
3rd-order harmonic distortion	f = 50 MHz		-61	dBc	
	f = 100 MHz	-49			
2nd-order intermodulation distortion		f <sub>C</sub> = 70 MHz	-78		
3rd-order intermodulation distortion	$V_O = 1 V_{PP}$	f <sub>C</sub> = 140 MHz	-55	-ID-	
	200 kHz Tone spacing, $R_L = 100 \Omega$	f <sub>C</sub> = 70 MHz	-82	dBc	
	_	f <sub>C</sub> = 140 MHz	-65		
Ond and a set of interest and a		f <sub>C</sub> = 70 MHz	70.2	dBm	0
2nd-order output intercept point	200 kHz Tone spacing	f <sub>C</sub> = 140 MHz	47		С
Ond	R <sub>L</sub> = 100 Ω	f <sub>C</sub> = 70 MHz	32.7		
3rd-order output intercept point		f <sub>C</sub> = 140 MHz	24.7		
4 dD communication maint	f <sub>C</sub> = 70 MHz		3	-ID	
1-dB compression point	f <sub>C</sub> = 140 MHz		2	dBm	
Noise figure	50 Ω System, 10 MHz, G =	6 dB	19.8	dB	
Input voltage noise	f > 10 MHz		3.3	nV/√ <del>Hz</del>	
Input current noise	f > 10 MHz		1.7	pA/√ <del>Hz</del>	
DC PERFORMANCE					
Open-loop voltage gain (A <sub>OL</sub> )			68	dB	
Input offset voltage	T <sub>A</sub> = +25°C		1	mV	
Average offset voltage drift	$T_A = -40$ °C to +85°C		2.6	μV/°C	
Input bias current	T <sub>A</sub> = +25°C		6	μΑ	
Average bias current drift	$T_A = -40$ °C to +85°C		20	nA/°C	
Input offset current	T <sub>A</sub> = +25°C		1.6	μΑ	
Average offset current drift	$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$		4	nA/°C	
INPUT	·				
Common-mode input range high			0.4		
Common-mode input range low			-0.4	V	
Common-mode rejection ratio			90	dB	
Differential input impedance			1.3    1.8		
Common-mode input impedance			1.0    2.3	MΩ    pF	

<sup>(1)</sup> Test levels: (A) 100% tested at +25°C. Over-temperature limits by characterization and simulation. (B) Limits set by characterization and simulation. (C) Typical value only for information.

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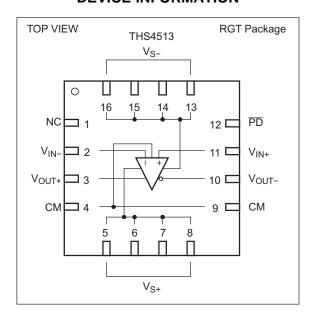


Test conditions at  $V_{S+}=1.5$  V,  $V_{S-}=-1.5$  V, G=0 dB, CM= open,  $V_{O}=1$  V<sub>PP</sub>,  $R_{F}=348$   $\Omega$ ,  $R_{L}=200$   $\Omega$  differential,  $T_{A}=+25^{\circ}C$ , single-ended input, differential output, and input and output referenced to mid-supply, unless otherwise noted.

PARAMETER			UNIT	TEST LEVEL <sup>(1)</sup>
OUTPUT				
Maximum output voltage high	Each output with 100 Ω to mid-supply	0.45	V	
Minimum output voltage low	Each output with 100 12 to min-supply	-0.45	V	
Differential output voltage swing		1.8	V	
Differential output current drive	$R_L = 10 \Omega$	50	mA	
Output balance error	V <sub>O</sub> = 100 mV, f = 1 MHz	-54	dB	
Closed-loop output Impedance	f = 1 MHz	0.3	Ω	1
OUTPUT COMMON-MODE VOLTAGE CO	ONTROL			1
Small-signal bandwidth		150	MHz	1
Slew rate		60	V/µs	1
Gain		1	V/V	1
Output common-mode offset from CM input	-0.5 V < CM < 0.5 V	4	mV	
CM input bias current	-0.5 V < CM < 0.5 V	±40	μΑ	1
CM input voltage range		-1.5 to 1.5	V	С
CM input impedance		20    1	kΩ    pF	
CM default voltage		0	V	
POWER SUPPLY				1
Quiescent current		34.8	mA	
Power-supply rejection (±PSRR)		80	dB	1
POWER-DOWN				1
Enable voltage threshold	Referenced to V <sub>s-</sub> , Assured <i>on</i> above 2.1 V + V <sub>S-</sub>	> 2.1	V	
Disable voltage threshold	Assured off below 0.7 V + V <sub>S</sub> _	< 0.7	V	
Power-down quiescent current		0.46	mA	1
Input bias current	PD = V <sub>S</sub> -	65	μΑ	
Input impedance		50    2	kΩ    pF	
Turn-on time delay	Measured to output on	100	ns	
Turn-off time delay	Measured to output off	10	μs	



#### **DEVICE INFORMATION**



## **TERMINAL FUNCTIONS**

	TERMINAL (RGT PACKAGE) DESCRIPTION	
NO.	NAME	
1	NC	No internal connection
2	V <sub>IN</sub> _	Inverting amplifier input
3	$V_{OUT+}$	Noninverting amplifier output
4, 9	CM	Common-mode voltage input
5-8	V <sub>S+</sub>	Positive amplifier power-supply input
10	$V_{OUT-}$	Inverted amplifier output
11	$V_{IN+}$	Noninverting amplifier input
12	PD	Power-down, $\overline{PD}$ = logic low puts part into low-power mode, $\overline{PD}$ = logic high or open for normal operation
13-16	V <sub>S-</sub>	Negative amplifier power-supply input



## TYPICAL AC PERFORMANCE: $V_{S+} - V_{S-} = 5 \text{ V}$

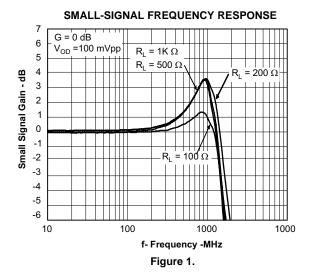
Test conditions at  $V_{S+}$  = +2.5 V,  $V_{S-}$  = -2.5V, CM = open,  $V_O$  = 2  $V_{PP}$ ,  $R_F$  = 348  $\Omega$ ,  $R_L$  = 200  $\Omega$  differential, G = 0 dB, single-ended input, and input and output referenced to mid-supply, unless otherwise noted.

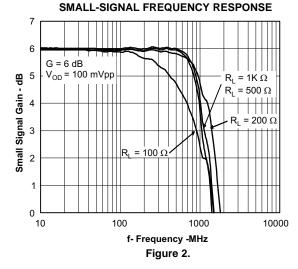
Small-Signal Frequency	$G = 0 dB, V_{OD} = 100 mV_{PP}$		Figure 1
Response	$G = 6 \text{ dB}, V_{OD} = 100 \text{ mV}_{PP}$		Figure 2
Large-Signal Frequency	$G = 0 dB$ , $V_{OD} = 2 V_{PP}$		Figure 3
Response	$G = 6 dB$ , $V_{OD} = 2 V_{PP}$		Figure 4
	$HD_2$ , $G = 0$ dB, $V_{OD} = 2$ $V_{PP}$	vs Frequency	Figure 5
	$HD_3$ , $G = 0$ dB, $V_{OD} = 2$ $V_{PP}$	vs Frequency	Figure 6
	$HD_2$ , $G = 6 dB$ , $V_{OD} = 2 V_{PP}$	vs Frequency	Figure 7
Harmonic	$HD_3$ , $G = 6 dB$ , $V_{OD} = 2 V_{PP}$	vs Frequency	Figure 8
Distortion	$HD_2$ , $G = 0 dB$	vs Output Voltage	Figure 9
	$HD_3$ , $G = 0 dB$	vs Output Voltage	Figure 10
	$HD_2$ , $G = 0 dB$	vs CM Output Voltage	Figure 11
	HD <sub>3</sub> , G = 0 dB	vs CM Output Voltage	Figure 12
Intermodulation	$IMD_2$ , $G = 0 dB$	vs Frequency	Figure 13
Distortion	$IMD_3$ , $G = 0 dB$	vs Frequency	Figure 14
Outrost Internation Bridge	OIP <sub>2</sub>	vs Frequency	Figure 15
Output Intercept Point	OIP <sub>3</sub>	vs Frequency	Figure 16
S-Parameters	,	vs Frequency	Figure 17
Transition Rate		vs Output Voltage	Figure 18
Transient Response		·	Figure 19
Settling Time			Figure 20
Rejection Ratio		vs Frequency	Figure 21
Output Impedance		vs Frequency	Figure 22
Overdrive Recovery			Figure 23
Output Voltage Swing		vs Load Resistance	Figure 24
Turn-Off Time		·	Figure 25
Turn-On Time			Figure 26
Input Offset Voltage		vs Input Common-Mode Voltage	Figure 27
Open-Loop Gain		vs Frequency	Figure 28
Input-Referred Noise		vs Frequency	Figure 29
Noise Figure		vs Frequency	Figure 30
Quiescent Current		vs Supply Voltage	Figure 31
Power-Supply Current		vs Supply Voltage in Power-Down Mode	Figure 32
Output Balance Error		vs Frequency	Figure 33
CM Input Impedence		vs Frequency	Figure 34
CM Small-Signal Frequency	Response		Figure 35
CM Input Bias Current		vs CM Input Voltage	Figure 36
Differential Output Offset Vol	tage	vs CM Input Voltage	Figure 37
Output Common-Mode Offse	et	vs CM Input Voltage	Figure 38

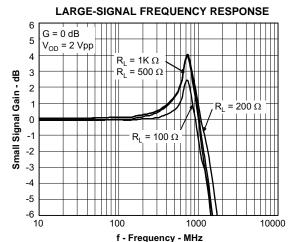


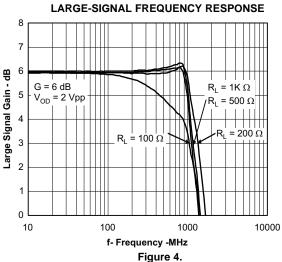
## TYPICAL CHARACTERISTICS: $V_{S+} - V_{S-} = 5 \text{ V}$

Test conditions at  $V_{S+}$  = +2.5 V,  $V_{S-}$  = -2.5V, CM = open,  $V_{O}$  = 2  $V_{PP}$ ,  $R_{F}$  = 348  $\Omega$ ,  $R_{L}$  = 200  $\Omega$  differential, G = 0 dB, single-ended input, and input and output referenced to mid-supply, unless otherwise noted.









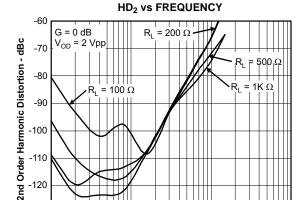
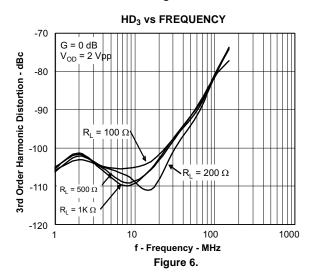


Figure 3.



f - Frequency - MHz

Figure 5.

100

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10

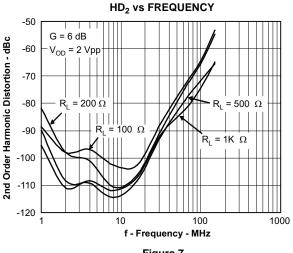
120

-130

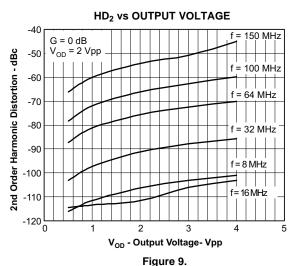
1000



Test conditions at  $V_{S+}$  = +2.5 V,  $V_{S-}$  = -2.5V, CM = open,  $V_O$  = 2  $V_{PP}$ ,  $R_F$  = 348  $\Omega$ ,  $R_L$  = 200  $\Omega$  differential, G = 0 dB, single-ended input, and input and output referenced to mid-supply, unless otherwise noted.







HD<sub>2</sub> vs OUTPUT COMMON-MODE VOLTAGE

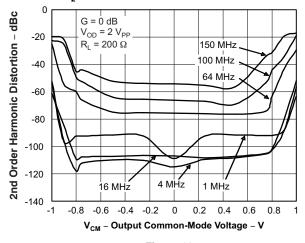
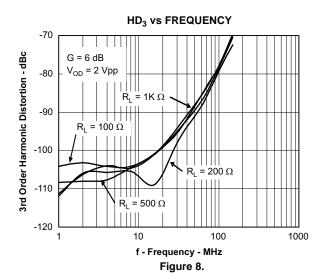
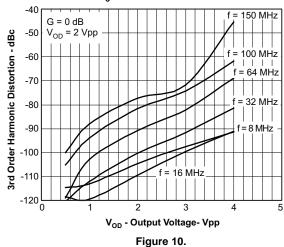


Figure 11.



HD<sub>3</sub> vs OUTPUT VOLTAGE



HD<sub>3</sub> vs OUTPUT COMMON-MODE VOLTAGE

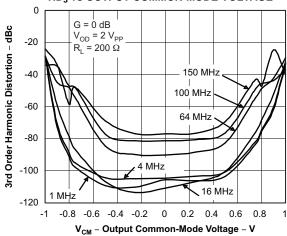
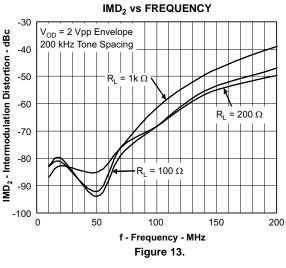
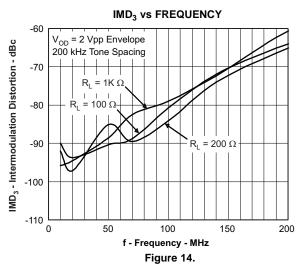


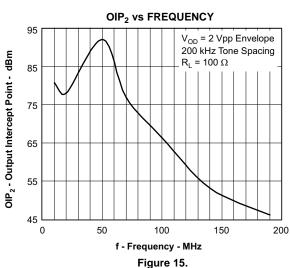
Figure 12.

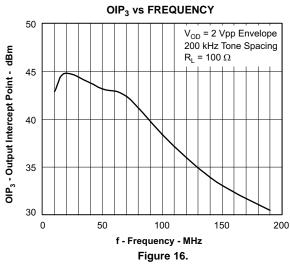


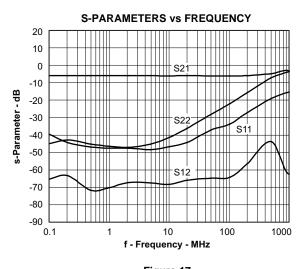
Test conditions at  $V_{S+}$  = +2.5 V,  $V_{S-}$  = -2.5V, CM = open,  $V_O$  = 2  $V_{PP}$ ,  $R_F$  = 348  $\Omega$ ,  $R_L$  = 200  $\Omega$  differential, G = 0 dB, single-ended input, and input and output referenced to mid-supply, unless otherwise noted.











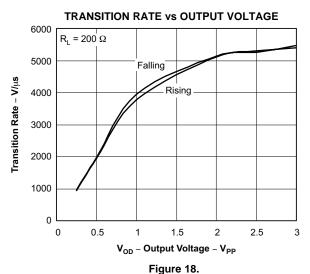
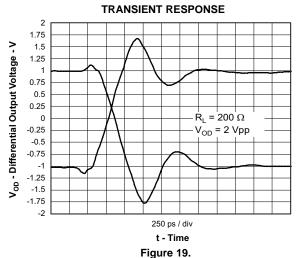


Figure 17.

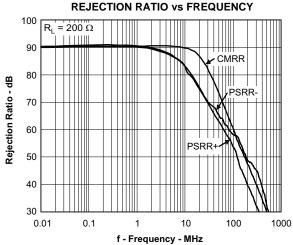
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Test conditions at  $V_{S+}$  = +2.5 V,  $V_{S-}$  = -2.5V, CM = open,  $V_O$  = 2  $V_{PP}$ ,  $R_F$  = 348  $\Omega$ ,  $R_L$  = 200  $\Omega$  differential, G = 0 dB, single-ended input, and input and output referenced to mid-supply, unless otherwise noted.

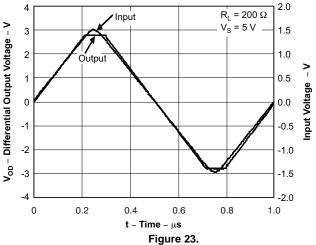


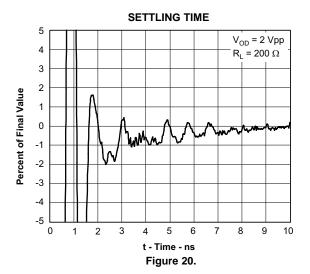




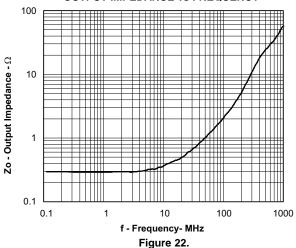
**OVERDRIVE RECOVERY** 

Figure 21.





#### **OUTPUT IMPEDANCE vs FREQUENCY**



#### **OUTPUT VOLTAGE SWING vs LOAD RESISTANCE**

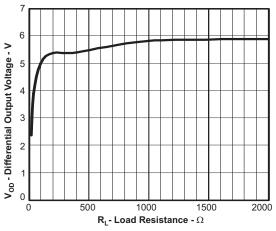
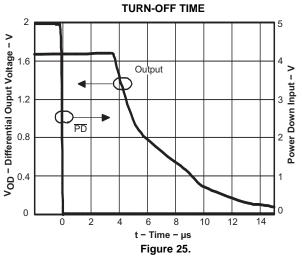
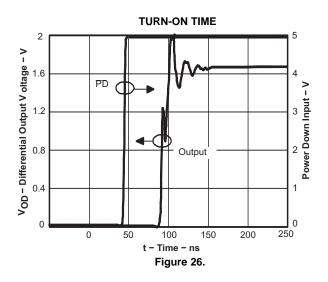


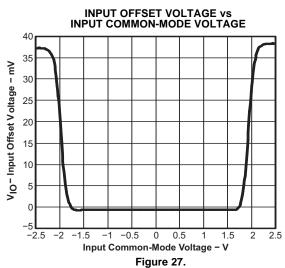
Figure 24.

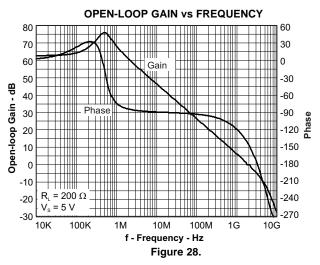


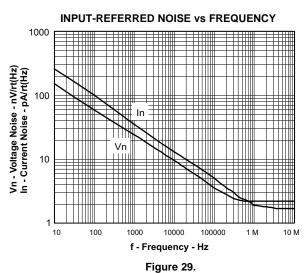
Test conditions at  $V_{S+}$  = +2.5 V,  $V_{S-}$  = -2.5V, CM = open,  $V_O$  = 2  $V_{PP}$ ,  $R_F$  = 348  $\Omega$ ,  $R_L$  = 200  $\Omega$  differential, G = 0 dB, single-ended input, and input and output referenced to mid-supply, unless otherwise noted.

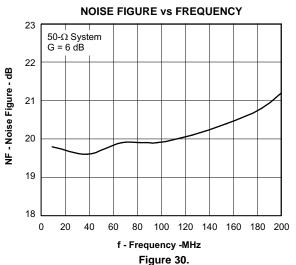












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Test conditions at  $V_{S+}$  = +2.5 V,  $V_{S-}$  = -2.5 V, CM = open,  $V_O$  = 2  $V_{PP}$ ,  $R_F$  = 348  $\Omega$ ,  $R_L$  = 200  $\Omega$  differential, G = 0 dB, single-ended input, and input and output referenced to mid-supply, unless otherwise noted.

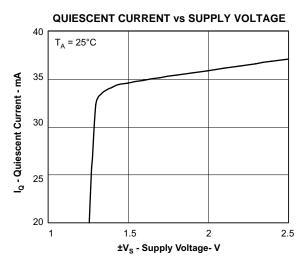
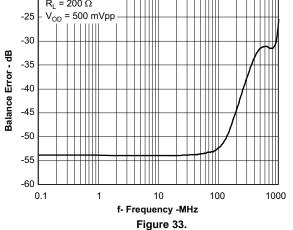
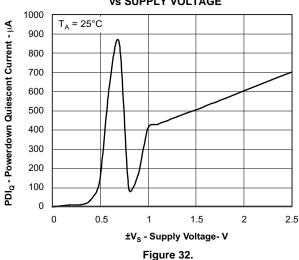


Figure 31.

# OUTPUT BALANCE ERROR RESPONSE vs FREQUENCY $^{-20}$ $_{\text{R}_1} = 200 \, \Omega$



## POWER-DOWN QUIESCENT CURRENT vs SUPPLY VOLTAGE



CM INPUT IMPEDANCE vs FREQUENCY

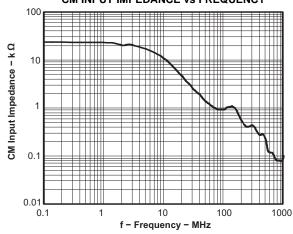
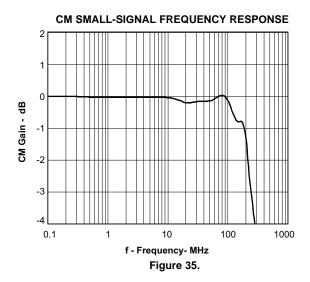
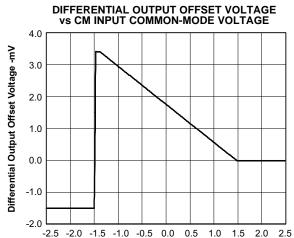


Figure 34.

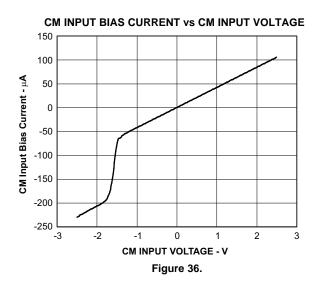


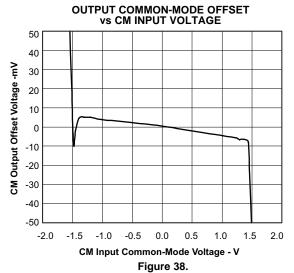
Test conditions at  $V_{S+}$  = +2.5 V,  $V_{S-}$  = -2.5 V, CM = open,  $V_{O}$  = 2  $V_{PP}$ ,  $R_{F}$  = 348  $\Omega$ ,  $R_{L}$  = 200  $\Omega$  differential, G = 0 dB, single-ended input, and input and output referenced to mid-supply, unless otherwise noted.













## TYPICAL AC PERFORMANCE: $V_{S+} - V_{S-} = 3 \text{ V}$

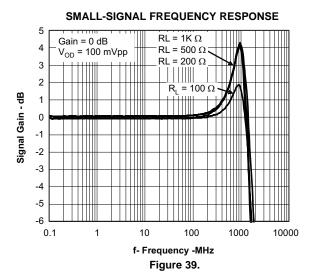
Test conditions at  $V_{S+}$  = +1.5 V,  $V_{S-}$  = -1.5V, CM = open,  $V_{OD}$  = 1  $V_{PP}$ ,  $R_F$  = 348  $\Omega$ ,  $R_L$  = 200  $\Omega$  differential, G = 0 dB, single-ended input, and input and output referenced to mid-supply, unless otherwise noted.

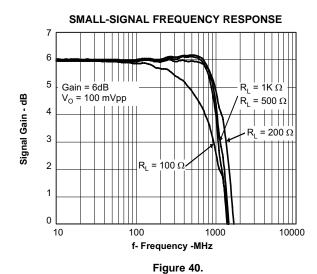
Small-Signal Frequency Response	$G = 0 \text{ dB}, V_{OD} = 100 \text{ mV}_{PP}$		Figure 39
Small-Signal Frequency Response	$G = 6 dB$ , $V_{OD} = 100 mV_{PP}$	Figure 40	
Large-Signal Frequency Response	$G = 0 dB$ , $V_{OD} = 1 V_{PP}$		Figure 41
Large-Signal Frequency Response	$G = 6 dB$ , $V_{OD} = 1 V_{PP}$		Figure 42
	$HD_2$ , $G = 0$ $dB$ , $V_{OD} = 1$ $V_{PP}$	vs Frequency	Figure 43
	$HD_3$ , $G = 0$ $dB$ , $V_{OD} = 1$ $V_{PP}$	vs Frequency	Figure 44
	$HD_2$ , $G = 6 dB$ , $V_{OD} = 1 V_{PP}$	vs Frequency	Figure 45
Harmonic	$HD_3$ , $G = 6$ dB, $V_{OD} = 1$ $V_{PP}$	vs Frequency	Figure 46
Distortion	$HD_2$ , $G = 0 dB$	vs Output Voltage	Figure 47
	$HD_3$ , $G = 0 dB$	vs Output Voltage	Figure 48
	$HD_2$ , $G = 0 dB$	vs CM Output Voltage	Figure 49
	$HD_3$ , $G = 0 dB$	vs CM Output Voltage	Figure 50
Intermodulation	$IMD_2$ , $G = 0 dB$	vs Frequency	Figure 51
Distortion	$IMD_3$ , $G = 0 dB$	vs Frequency	Figure 52
Ouput Intercept Point	OIP <sub>2</sub>	vs Frequency	Figure 53
Ouput intercept Point	OIP <sub>3</sub>	vs Frequency	Figure 54
S-Parameters		vs Frequency	Figure 55
Transition Rate		vs Output Voltage	Figure 56
Transient Response			Figure 57
Settling Time			Figure 58
Output Voltage Swing		vs Load Resistance	Figure 59
Rejection Ratio		vs Frequency	Figure 60
Overdrive Recovery			Figure 61
Output Impedance		vs Frequency	Figure 62
Turn-Off Time			Figure 63
Turn-On Time			Figure 64
Ouput Balance Error		vs Frequency	Figure 65
Noise Figure		vs Frequency	Figure 66
CM Small-Signal Frequency Respon	se		Figure 67
CM Input Impedance		vs Frequency	Figure 68
Differential Output Offset Voltage		vs CM Input Voltage	Figure 69
Output Common-Mode Offset		vs CM Input Voltage	Figure 70



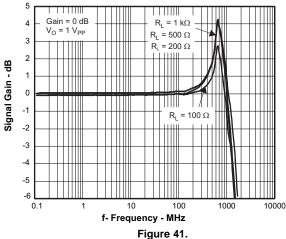
## TYPICAL CHARACTERISTICS: $V_{S+} - V_{S-} = 3 \text{ V}$

Test conditions at  $V_{S+}$  = +1.5 V,  $V_{S-}$  = -1.5V, CM = open,  $V_{OD}$  = 1  $V_{PP}$ ,  $R_F$  = 348  $\Omega$ ,  $R_L$  = 200  $\Omega$  differential, G = 0 dB, single-ended input, and input and output referenced to mid-supply, unless otherwise noted.









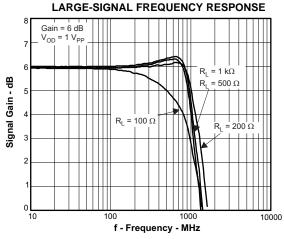
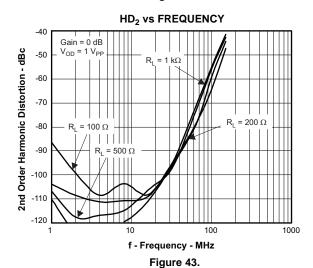


Figure 42.



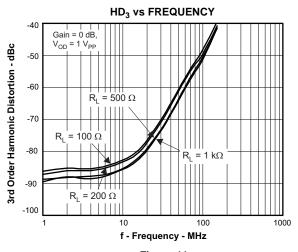


Figure 44.



Test conditions at  $V_{S+}$  = +1.5 V,  $V_{S-}$  = -1.5V, CM = open,  $V_{OD}$  = 1  $V_{PP}$ ,  $R_F$  = 348  $\Omega$ ,  $R_L$  = 200  $\Omega$  differential, G = 0 dB, single-ended input, and input and output referenced to mid-supply, unless otherwise noted.

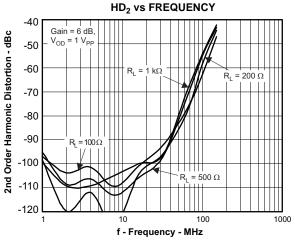


Figure 45.

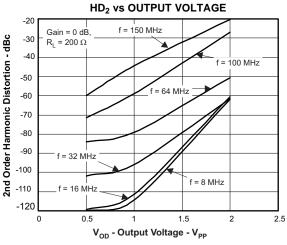


Figure 47.

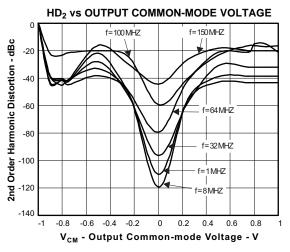
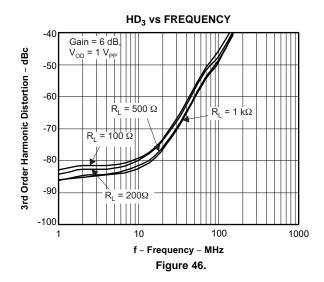
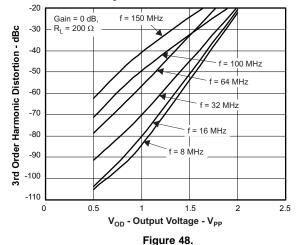


Figure 49.







HD<sub>3</sub> vs OUTPUT COMMON-MODE VOLTAGE

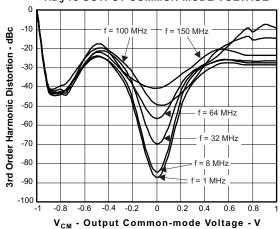


Figure 50.



Test conditions at  $V_{S+}$  = +1.5 V,  $V_{S-}$  = -1.5V, CM = open,  $V_{OD}$  = 1  $V_{PP}$ ,  $R_F$  = 348  $\Omega$ ,  $R_L$  = 200  $\Omega$  differential, G = 0 dB, single-ended input, and input and output referenced to mid-supply, unless otherwise noted.

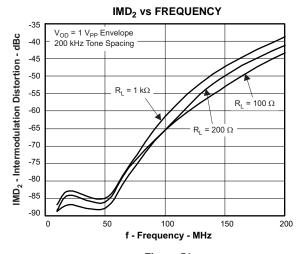
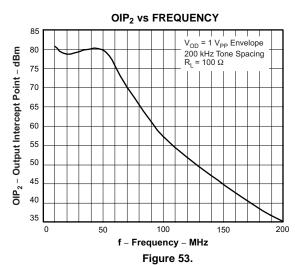
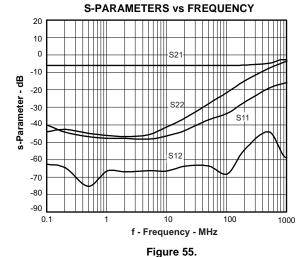
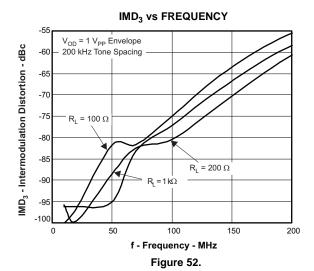
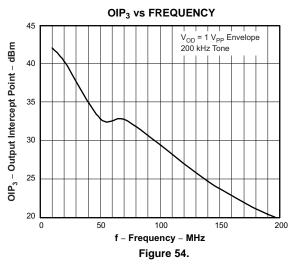


Figure 51.









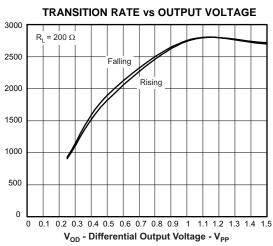


Figure 56.



Test conditions at  $V_{S+}$  = +1.5 V,  $V_{S-}$  = -1.5V, CM = open,  $V_{OD}$  = 1  $V_{PP}$ ,  $R_F$  = 348  $\Omega$ ,  $R_L$  = 200  $\Omega$  differential, G = 0 dB, single-ended input, and input and output referenced to mid-supply, unless otherwise noted.

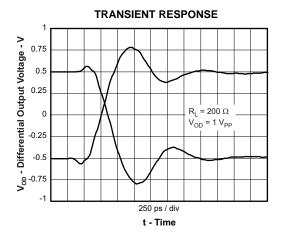


Figure 57.

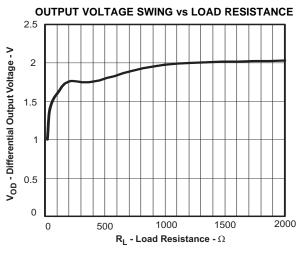
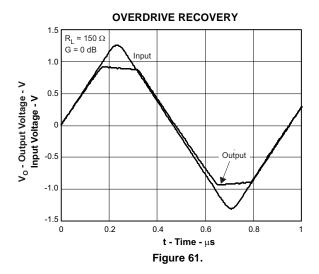
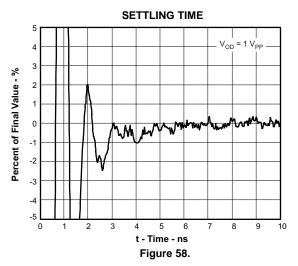


Figure 59.





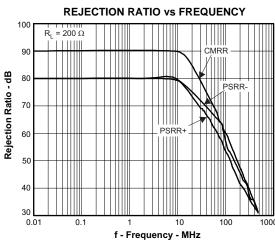


Figure 60.

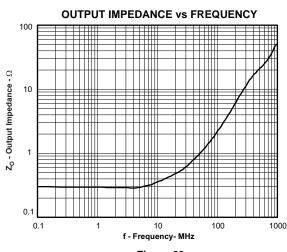
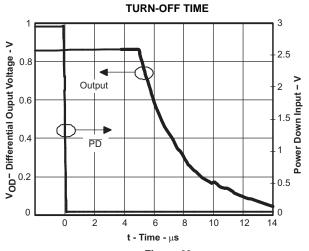


Figure 62.



Test conditions at  $V_{S+}$  = +1.5 V,  $V_{S-}$  = -1.5V, CM = open,  $V_{OD}$  = 1  $V_{PP}$ ,  $R_F$  = 348  $\Omega$ ,  $R_L$  = 200  $\Omega$  differential, G = 0 dB, single-ended input, and input and output referenced to mid-supply, unless otherwise noted.



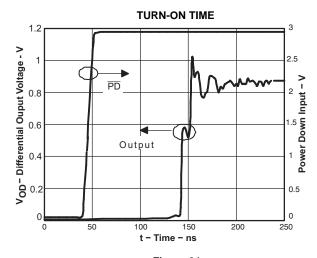


Figure 63.



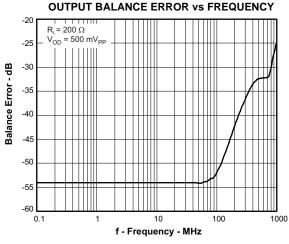


Figure 64.

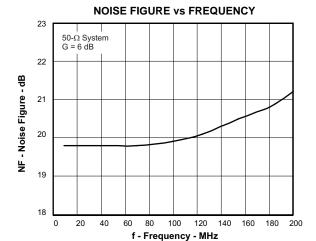


Figure 65.

**CM SMALL-SIGNAL FREQUENCY RESPONSE** 

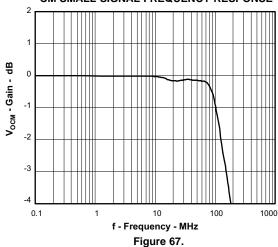


Figure 66.

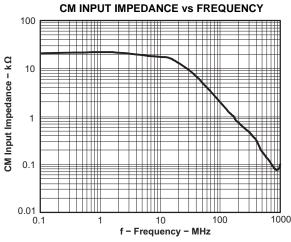
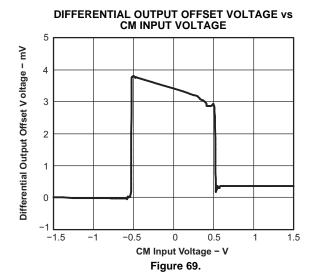
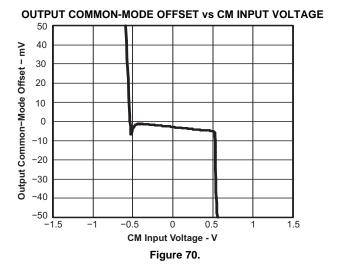


Figure 68.



Test conditions at  $V_{S+}$  = +1.5 V,  $V_{S-}$  = -1.5V, CM = open,  $V_{OD}$  = 1  $V_{PP}$ ,  $R_F$  = 348  $\Omega$ ,  $R_L$  = 200  $\Omega$  differential, G = 0 dB, single-ended input, and input and output referenced to mid-supply, unless otherwise noted.





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#### **TEST CIRCUITS**

The THS4513 is tested with the following test circuits built on the EVM. For simplicity, power-supply decoupling is not shown-see Recommendations in the applications section for recommendations. Depending on the test conditions, component values are changed per the following tables, or as otherwise noted. The signal generators used are ac-coupled,  $50-\Omega$  sources and a  $0.22-\mu F$ capacitor and a 49.9-Ω resistor to ground are inserted across R<sub>IT</sub> on the alternate input to balance the circuit. A split power supply is used to ease the interface to common test equipment, but the amplifier can be operated single-supply as described in the applications section with no impact on performance.

**Table 1. Gain Component Values** 

GAIN	R <sub>F</sub>	R <sub>G</sub>	R <sub>IT</sub>
0 dB	348 Ω	340 Ω	56.2 Ω
6 dB	348 Ω	66.5 Ω	61.4 Ω

Note the gain setting includes 50- $\Omega$  source impedance. Components are chosen to achieve gain and 50- $\Omega$  input termination.

**Table 2. Load Component Values** 

R <sub>L</sub>	Ro	R <sub>OT</sub>	Atten.
100 Ω	25 Ω	Open	6 dB
200 Ω	86.6 Ω	69.8 Ω	16.8 dB
499 Ω	237 Ω	56.2 Ω	25.5 dB
1k Ω	487 Ω	52.3 Ω	31.8 dB

Note the total load includes  $50-\Omega$  termination by the test equipment. Components are chosen to achieve load and  $50-\Omega$  line termination through a 1:1 transformer.

Due to the voltage divider on the output formed by the load component values, the amplifier output is attenuated. The column *Atten* in Table 2 shows the attenuation expected from the resistor divider. When using a transformer at the output as shown in Figure 72, the signal will see slightly more loss, and these numbers will be approximate.

#### **Frequency Response**

The circuit shown in Figure 71 is used to measure the frequency response of the circuit.

A network analyzer is used as the signal source and as the measurement device. The output impedance of the network analyzer is 50  $\Omega.$   $R_{\text{IT}}$  and  $R_{G}$  are chosen to impedance match to 50  $\Omega,$  and to maintain the proper gain. To balance the amplifier, a 0.22- $\mu F$  capacitor and 49.9- $\Omega$  resistor to ground are inserted across  $R_{\text{IT}}$  on the alternate input.

The output is probed using a high-impedance differential probe across the  $100-\Omega$  resistor. The gain is referred to the amplifier output by adding back the 6-dB loss due to the voltage divider on the output.

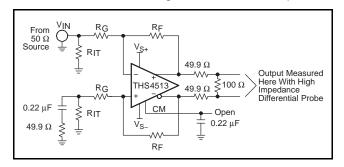


Figure 71. Frequency Response Test Circuit

#### **Distortion and 1-dB Compression**

The circuit shown in Figure 72 is used to measure harmonic distortion, intermodulation distortion, and 1-db compression point of the amplifier.

A signal generator is used as the signal source and the output is measured with a spectrum analyzer. The output impedance of the signal generator is 50  $\Omega.$   $R_{\text{IT}}$  and  $R_{G}$  are chosen to impedance-match to 50  $\Omega,$  and to maintain the proper gain. To balance the amplifier, a 0.22- $\mu\text{F}$  capacitor and 49.9- $\Omega$  resistor to ground are inserted across  $R_{\text{IT}}$  on the alternate input.

A low-pass filter is inserted in series with the input to reduce harmonics generated at the signal source. The level of the fundamental is measured, then a high-pass filter is inserted at the output to reduce the fundamental so that it does not generate distortion in the input of the spectrum analyzer.

The transformer used in the output to convert the signal from differential to single-ended is an ADT1-1WT. It limits the frequency response of the circuit so that measurements cannot be made below approximately 1 MHz.

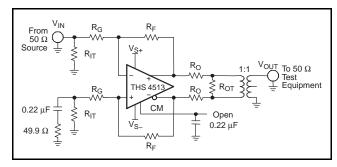


Figure 72. Distortion Test Circuit



The 1-dB compression point is measured with a spectrum analyzer with 50- $\Omega$  double termination or 100- $\Omega$  termination; see Table 2. The input power is increased until the output is 1 dB lower than expected. The number reported in the table data is the power delivered to the spectrum analyzer input. Add 3 dB to refer to the amplifier output.

#### S-Parameter, Slew Rate, Transient Response, Settling Time, Output Impedance, Overdrive, Output Voltage, and Turn-On/Off Time

The circuit shown in Figure 73 is used to measure s-parameters, slew rate, transient response, settling time, output impedance, overdrive recovery, output voltage swing, and turn-on/turn-off times of the amplifier. For output impedance, the signal is injected at  $V_{OUT}$  with  $V_{IN}$  left open and the drop across the 49.9  $\Omega$  resistor is used to calculate the impedance seen looking into the amplifier output.

Because  $S_{21}$  is measured single-ended at the load with  $50-\Omega$  double termination, add 12 dB to refer to the amplifier's output as a differential signal.

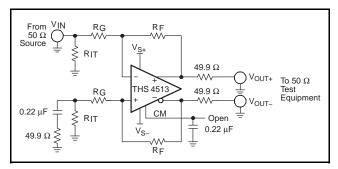


Figure 73. S-Parameter, SR, Transient Response, Settling Time, Z<sub>0</sub>, Overdrive Recovery, V<sub>OUT</sub> Swing, and Turn-On/Off Test Circuit

#### **CM** Input

The circuit shown in Figure 74 is used to measure the frequency response and input impedance of the CM input. Frequency response is measured single-ended

at  $V_{OUT+}$  or  $V_{OUT-}$  with the input injected at  $V_{IN}$ ,  $R_{CM}$  = 0  $\Omega$  and  $R_{CMT}$  = 49.9  $\Omega$ . The input impedance is measured with  $R_{CM}$  = 49.9  $\Omega$  with  $R_{CMT}$  = open, and calculated by measuring the voltage drop across  $R_{CM}$  to determine the input current.

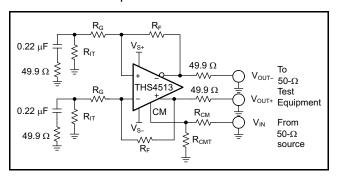


Figure 74. CM Input Test Circuit

#### **CMRR and PSRR**

The circuit shown in Figure 75 is used to measure the CMRR and PSRR of  $V_{S+}$  and  $V_{S-}$ . The input is switched appropriately to match the test being performed.

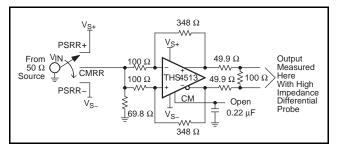


Figure 75. CMRR and PSRR Test Circuit



#### **APPLICATION INFORMATION**

#### **APPLICATIONS**

The following circuits show application information for the THS4513. For simplicity, power-supply decoupling capacitors are not shown in these diagrams. Please see the *THS4513 EVM* section for recommendations. For more detail on the use and operation of fully differential op amps refer to application report *Fully-Differential Amplifiers* (SLOA054).

#### **Differential Input to Differential Output Amplifier**

The THS4513 is a fully differential op amp, and can be used to amplify differential input signals to differential output signals. A basic block diagram of the circuit is shown in Figure 76 (CM input not shown). The gain of the circuit is set by  $R_{\text{\tiny F}}$  divided by  $R_{\text{\tiny G}}.$ 

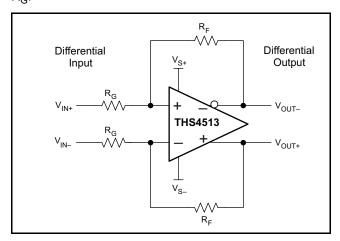


Figure 76. Differential Input to Differential Ouput Amplifier

Depending on the source and load, input and output termination can be accomplished by adding  $R_{\text{IT}}$  and  $R_{\text{O}}$ .

# Single-Ended Input to Differential Output Amplifier

The THS4513 can be used to amplify and convert single-ended input signals to differential output signals. A basic block diagram of the circuit is shown in Figure 77 (CM input not shown). The gain of the circuit is again set by  $R_{\text{F}}$  divided by  $R_{\text{G}}.$ 

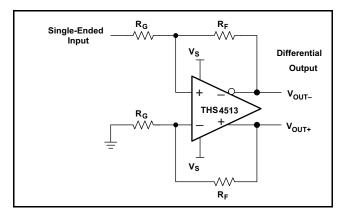


Figure 77. Single-Ended Input to Differential Output Amplifier

#### Input Common-Mode Voltage Range

The input common-model voltage of a fully differential op amp is the voltage at the '+' and '-' input pins of the op amp.

It is important to not violate the input common-mode voltage range ( $V_{ICR}$ ) of the op amp. Assuming the op amp is in linear operation the voltage across the input pins is only a few millivolts at most. So finding the voltage at one input pin will determine the input common-mode voltage of the op amp.

Treating the negative input as a summing node, the voltage is given by Equation 1:

$$V_{IC} = \left(V_{OUT+} \times \frac{R_G}{R_G + R_F}\right) + \left(V_{IN-} \times \frac{R_F}{R_G + R_F}\right) \tag{1}$$

To determine the  $V_{ICR}$  of the op amp, the voltage at the negative input is evaluated at the extremes of  $V_{OUT+}$ .

As the gain of the op amp increases, the input common-mode voltage becomes closer and closer to the input common-mode voltage of the source.



#### **Setting the Output Common-Mode Voltage**

The output common-mode voltage is set by the voltage at the CM pin(s). The internal common-mode control circuit maintains the output common-mode voltage within 3-mV offset (typ) from the set voltage, when set within 0.5 V of mid-supply, with less than 4-mV differential offset voltage. If left unconnected, the common-mode set point is set to mid-supply by internal circuitry, which may be over-driven from an external source. Figure 78 is representative of the CM input. The internal CM circuit has about 700 MHz of -3-dB bandwidth, which is required for best performance, but it is intended to be a dc bias input pin. Bypass capacitors are recommended on this pin to reduce noise at the output. The external current required to overdrive the internal resistor divider is given by Equation 2:

$$I_{EXT} = \frac{2V_{CM} - (V_{S+} - V_{S-})}{50 \text{ k}\Omega}$$
 (2)

where V<sub>CM</sub> is the voltage applied to the CM pin.

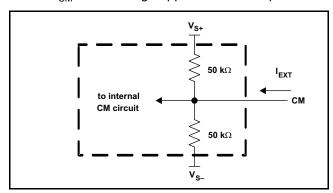


Figure 78. CM Input Circuit

#### Single-Supply Operation (3 V to 5 V)

To facilitate testing with common lab equipment, the THS4513 EVM allows split-supply operation, and the characterization data presented in this data sheet was taken with split-supply power inputs. The device can easily be used with a single-supply power input without degrading the performance. Figure 79, Figure 80, and Figure 81 show dc and ac-coupled single-supply circuits with single-ended inputs. These configurations all allow the input and output common-mode voltage to be set to mid-supply allowing for optimum performance. The information presented here can also be applied to differential input sources.

In Figure 79, the signal source is referenced to a voltage derived from the CM pin via a unity-gain wideband buffer such as the BUF602.  $V_{CM}$  is set to mid-supply by THS4513 internal circuitry.  $R_{T}$  along with the input impedance of the amplifier provides input termination, which is also referenced to  $V_{CM}$ .

Note that  $R_S$  and  $R_T$  are added to the alternate input from the signal input to balance the amplifier. Alternately, one resistor can be used equal to the combined value  $R_G + R_S \mid\mid R_T$  on this input. This is also true of the circuits shown in Figure 80 and Figure 81.

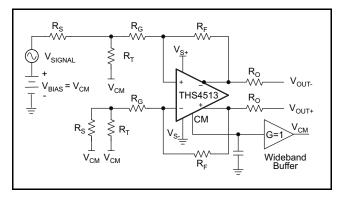


Figure 79. THS4513 DC-Coupled Single-Supply with Input Biased to  $V_{CM}$ 

In Figure 80 the source is referenced to ground and so is the input termination resistor.  $R_{PU}$  is added to the circuit to avoid violating the  $V_{ICR}$  of the op amp. The proper value of resistor to add can be calculated from Equation 3:

$$R_{PU} = \frac{(V_{IC} - V_{S+})}{V_{CM} \left(\frac{1}{R_F}\right) - V_{IC} \left(\frac{1}{R_{IN}} + \frac{1}{R_F}\right)}$$
(3)

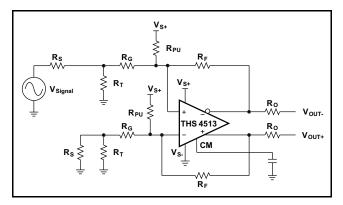


Figure 80. THS4513 DC-Coupled Single-Supply with  $R_{PU}$  Used to Set  $V_{IC}$ 

 $V_{IC}$  is the desired input common-mode voltage,  $V_{CM}$  = CM, and  $R_{IN}$  =  $R_G$ +  $R_S$  ||  $R_T$ . To set to mid-supply, make the value of  $R_{PU}$  =  $R_G$ +  $R_S$  ||  $R_T$ .

Table 3 is a modification of Table 1 to add the proper values with  $R_{PU}$  assuming a  $50-\Omega$  source impedance and setting the input and output common-mode voltage to mid-supply.



There are two drawbacks to this configuration. One is that it requires additional current from the power supply. Using the values shown for a gain of 0 dB requires 14 mA more current with 5 V supply, and 8.2 mA more current with 3 V supply.

The other drawback is this configuration also increases the noise gain of the circuit. In the 10-dB gain case, noise gain increases by a factor of 1.5.

Table 3. R<sub>PU</sub> Values for Various Gains

Gain	R <sub>F</sub>	$R_G$	R <sub>IT</sub>	R <sub>PU</sub>
0 dB	348 Ω	340 Ω	56.2 Ω	365 Ω
6 dB	348 Ω	168 Ω	64.9 Ω	200 Ω

Figure 81 shows ac-coupling to the source. Using capacitors in series with the termination resistors allows the amplifier to self-bias both input and output to mid-supply.

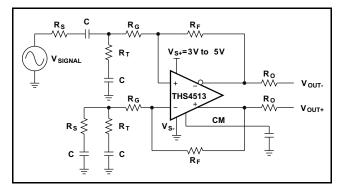


Figure 81. THS4513 AC-Coupled Single-Supply

#### Low-Pass Filter

One application for the THS4513 is as a unity-gain buffer with low-pass filtering. Figure 82 shows a circuit that is driven by an ac-coupled  $50\text{-}\Omega$  source. A 1:1 transformer converts the differential output of the THS4513 into a single-ended output capable of driving  $50\text{-}\Omega$  test equipment. The circuit as shown has an overall gain of -6 dB due to the voltage divider on the device output, and has a roll-off frequency of approximately 60 MHz. The measured gain versus frequency response of the overall circuit is shown in Figure 83. The low-frequency roll-off is due to losses in the output transformer at those frequencies.

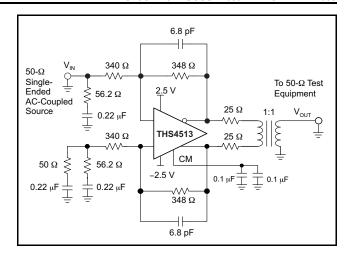


Figure 82. 60-MHz Low-Pass Filter

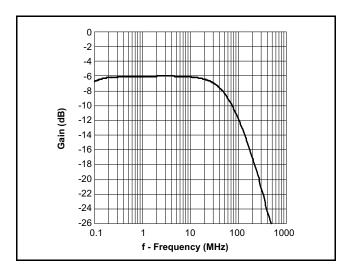


Figure 83. Low-Pass Filter Measured Frequency Response



#### THS4513 + ADS5500 Combined Performance

The THS4513 is designed to be a high performance drive amplifier for high performance data converters like the ADS5500 14-bit 125-MSPS ADC. Figure 84 shows a circuit combining the two devices. The THS4513 amplifier circuit provides 10 dB of gain, converts the single-ended input to differential, and sets the proper input common-mode voltage to the ADS5500. The  $100-\Omega$  resistors and 2.7-pF capacitor between the THS4513 outputs and ADS5500 inputs along with the input capacitance of the ADS5500 limit the bandwidth of the signal to 115 MHz (-3 dB). For testing, a signal generator is used for the signal source. The generator is an ac-coupled  $50-\Omega$  source. A band-pass filter is inserted in series with the input to reduce harmonics and noise from the signal source. Input termination is accomplished via the 69.8-Ω resistor and 0.22-μF capacitor to ground in conjunction with the input impedance of the amplifier circuit. A  $0.22-\mu F$  capacitor and  $49.9-\Omega$  resistor is inserted to ground across the  $69.8-\Omega$  resistor and 0.22-µF capacitor on the alternate input to balance the circuit. Gain is a function of the source impedance, termination, and 348-Ω feedback resistor. Refer to Table 3 for component values to set proper  $50-\Omega$  termination for other common gains. A split power supply of +4 V and -1 V is used to set the input and output common-mode voltages approximately mid-supply while setting the input common-mode of the ADS5500 to the recommended +1.55 V. This maintains maximum headroom on the internal transistors of the THS4513 to insure optimum performance.

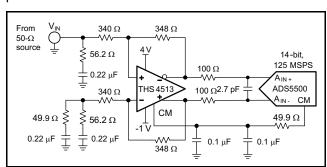


Figure 84. THS4513 + ADS5500 Circuit

Figure 85 shows the two-tone FFT of the THS4513 + ADS5500 circuit with 65 MHz and 70 MHz input frequencies. The SFDR is 90 dBc.

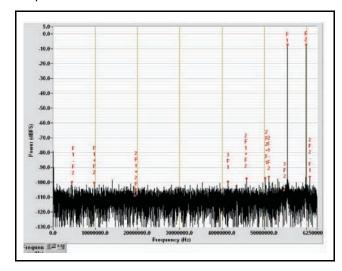


Figure 85. THS4513 and ADS5500 2-Tone FFT with 65 MHz and 70 MHz Input

#### THS4513 + ADS5424 Combined Performance

Figure 86 shows the THS4513 driving the ADS5424 ADC.

As before, the THS4513 amplifier provides 10 dB of gain, converts the single-ended input to differential, and sets the proper input common-mode voltage to the ADS5424. Input termination and circuit testing is the same as described above for the THS4513 + ADS5500 circuit.

The  $225-\Omega$  resistors and 2.7-pF capacitor between the THS4513 outputs and ADS5424 inputs (along with the input capacitance of the ADC) limit the bandwidth of the signal to about 100 MHz (-3 dB).

Since the ADS5424 recommended input common-mode voltage is 2.4 V, the THS4513 is operated from a single power-supply input with  $V_{S+} = 5$  V and  $V_{S-} = 0$  V (ground).

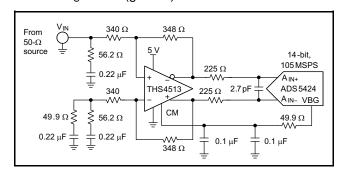


Figure 86. THS4513 + ADS5424 Circuit

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#### **Layout Recommendations**

It is recommended to follow the layout of the external components near the amplifier, ground plane construction, and power routing of the EVM as closely as possible. General guidelines are:

- 1. Signal routing should be direct and as short as possible into and out of the op amp circuit.
- 2. The feedback path should be short and direct avoiding vias.
- 3. Ground or power planes should be removed from directly under the amplifier input and output pins.
- 4. An output resistor is recommended on each output, as near to the output pin as possible.
- 5. Two 10-μF and two 0.1-μF power-supply decoupling capacitors should be placed as near to the power-supply pins as possible.

- Two 0.1-μF capacitors should be placed between the CM input pins and ground. This limits noise coupled into the pins. One each should be placed to ground near pin 4 and pin 9.
- 7. It is recommended to split the ground panel on layer 2 (L2) as shown below and to use a solid ground on layer 3 (L3). A single-point connection should be used between each split section on L2 and L3.
- 8. A single-point connection to ground on L2 is recommended for the input termination resistors R1 and R2. This should be applied to the input gain resistors if termination is not used.
- The THS4513 recommended PCB footprint is shown in the Land Pattern drawing at the end of this document.

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#### **THS4513 EVM**

Figure 87 is the THS4513 EVAL1 EVM schematic; layers 1 through 4 of the PCB are shown Figure 89, and Table 4 is the bill of material for the EVM as supplied from TI.

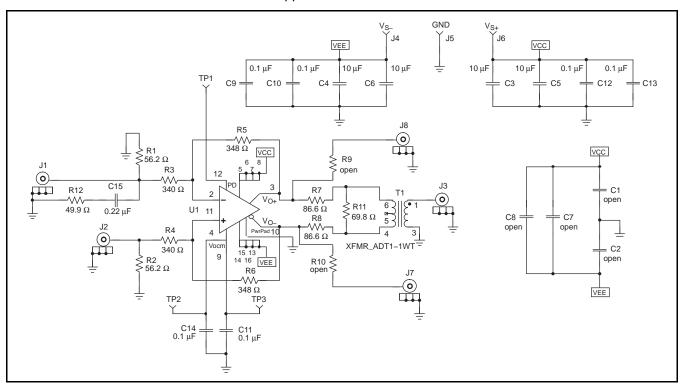


Figure 87. THS4513 EVAL1 EVM Schematic

Figure 88.

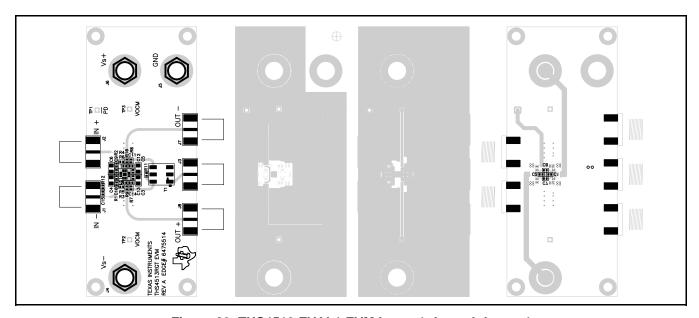


Figure 89. THS4513 EVAL1 EVM Layer 1 through Layer 4

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#### Table 4. THS4513 EVAL1 EVM Bill of Materials

ITEM	DESCRIPTION	SMD SIZE	REFERENCE DESIGNATOR	PCB QTY	MANUFACTURER PART NUMBER
1	CAP, 10.0 μF, Ceramic, X5R, 6.3 V	0805	C3, C4, C5, C6	4	(AVX) 08056D106KAT2A
2	CAP, 0.1 $\mu$ F, Ceramic, X5R, 10 V	0402	C9, C10, C11, C12, C13, C14	6	(AVX) 0402ZD104KAT2A
3	CAP, 0.22 $\mu$ F, Ceramic, X5R, 6.3 V	0402	C15	1	(AVX) 04026D224KAT2A
4	OPEN	0402	C1, C2, C7, C8	4	
5	OPEN	0402	R9, R10	2	
6	Resistor, 49.9 Ω, 1/16 W, 1%	0402	R12	1	(KOA) RK73H1ETTP49R9F
7	Resistor, 56.2 Ω, 1/16 W, 1%	0402	R1, R2	2	(KOA) RK73H1ETTP56R2F
8	Resistor, 69.8 Ω, 1/16 W, 1%	0402	R11	1	(KOA) RK73H1ETTP69R8F
9	Resistor, 86.6 Ω, 1/16 W, 1%	0402	R7, R8	2	(KOA) RK73H1ETTP86R6F
10	Resistor, 340 Ω, 1/16 W, 1%	0402	R3, R4	2	(KOA) RK73H1ETTP3400F
11	Resistor, 348 Ω, 1/16 W, 1%	0402	R5, R6	2	(KOA) RK73H1ETTP3480F
12	Transformer, RF		T1	1	(MINI-CIRCUITS) ADT1-1WT
13	Jack, banana receptance, 0.25" diameter hole		J4, J5, J6	3	(HH SMITH) 101
14	OPEN		J1, J7, J8	3	
15	Connector, edge, SMA PCB Jack		J2, J3	2	(JOHNSON) 142-0701-801
16	Test point, Red		TP1, TP2, TP3	3	(KEYSTONE) 5000
17	IC, THS4513		U1	1	(TI) THS4513RGT
18	Standoff, 4-40 HEX, 0.625" length			4	(KEYSTONE) 1808
19	SCREW, PHILLIPS, 4-40, 0.250"			4	SHR-0440-016-SN
20	Printed circuit board			1	(TI) EDGE# 6475514



## **Revision History**

Cł	hanges from Revision B (November 2006) to Revision C	Page
•	Updated document format	1
•	Added Related Products table	
•	Added footnote 1 to Absolute Maximum Ratings table.	2
•	Added V (volts) to unit column of ESD ratings rows in Absolute Maximum Ratings table	2
•	Changed $V_{S+} - V_{S-} = 5$ V <i>Input</i> specifications from 1.75 V typ (common-mode input range high) to 1.4 V typ; $-1.75$ V (common-mode input range low) to $-1.4$ V; 1.67 M $\Omega$    1.32 pF (differential input impedance) to 1.3 M $\Omega$    1.8 pF; 1.2 M $\Omega$    1.45 pF (common-mode input impedance) to 1.0 M $\Omega$    2.3 pF	
•	Added V (volts) to unit column of second differential output voltage swing row in Output section of $V_{S+} - V_{S-} = 5 \text{ V}$ specifications	3
•	Changed $V_{S+} - V_{S-} = 3 \text{ V }$ Input specifications from 0.75 V typ (common-mode input range high) to 0.4 V typ; -0.75 V (common-mode input range low) to -0.4 V	5
•	Added 1.3 M $\Omega$    1.8 pF (differential input impedance); 1.0 M $\Omega$    2.3 pF (common-mode input impedance) to $V_{S+} - V_{S-} = 3 \ V$ <i>Input</i> specifications	5
•	Changed y-axis of Figure 11 to match rest of curves	10
•	Changed y-axis of Figure 12 to match rest of curves	10
•	Added 1.0 at end of x-axis in Figure 23.	12
•	Changed last number in x-axis of Figure 46 from 100 to 1000	18
•	Changed last number in y-axis of Figure 53 from 90 to 35	19





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#### PACKAGING INFORMATION

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
THS4513RGTR	ACTIVE	QFN	RGT	16	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
THS4513RGTRG4	ACTIVE	QFN	RGT	16	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
THS4513RGTT	ACTIVE	QFN	RGT	16	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
THS4513RGTTG4	ACTIVE	QFN	RGT	16	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

#### **OTHER QUALIFIED VERSIONS OF THS4513:**

Space: THS4513-SP

NOTE: Qualified Version Definitions:

• Space - Radiation tolerant, ceramic packaging and qualified for use in Space-based application



#### TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
THS4513RGTR	QFN	RGT	16	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
THS4513RGTT	QFN	RGT	16	250	180.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2





\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
THS4513RGTR	QFN	RGT	16	3000	346.0	346.0	29.0
THS4513RGTT	QFN	RGT	16	250	190.5	212.7	31.8

# RGT (S-PQFP-N16) PLASTIC QUAD FLATPACK 3,15 2,85 3,15 2,85 PIN 1 INDEX AREA TOP AND BOTTOM 0,20 REF. -SEATING PLANE 0,08 0,05 0,00 $16X \frac{0,50}{0,30}$ 16 13 EXPOSED THERMAL PAD ⇘ $16X \ \frac{0,30}{0,18}$ 0,10 M 0,50 1,50 4203495/E 11/04

- NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - B. This drawing is subject to change without notice.
  - C. Quad Flatpack, No-leads (QFN) package configuration.
  - The package thermal pad must be soldered to the board for thermal and mechanical performance.

    See the Product Data Sheet for details regarding the exposed thermal pad dimensions.
  - E. Falls within JEDEC MO-220.



#### THERMAL PAD MECHANICAL DATA



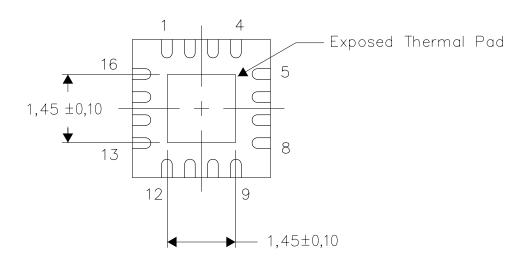
RGT (S-PVQFN-N16)

#### THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No—Lead (QFN) package and its advantages, refer to Application Report, Quad Flatpack No—Lead Logic Packages, Texas Instruments Literature No. SCBA017. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.

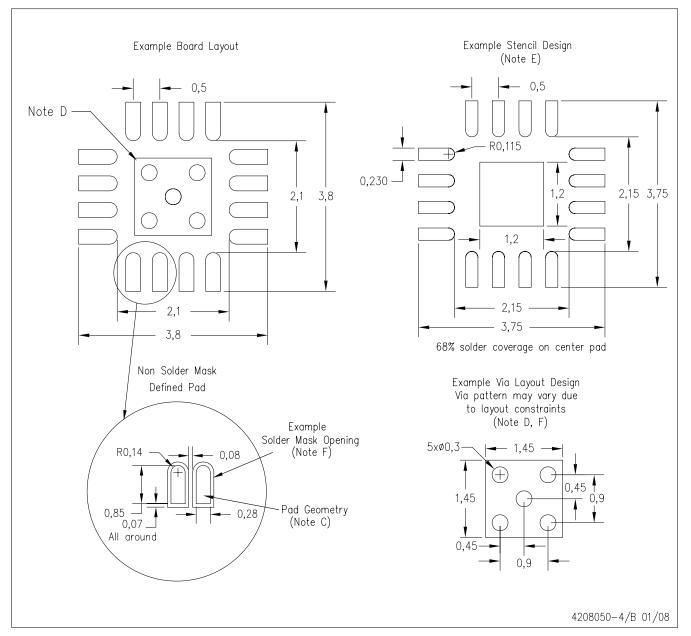


Bottom View

NOTE: All linear dimensions are in millimeters

Exposed Thermal Pad Dimensions

## RGT (S-PQFP-N16)



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat—Pack Packages, Texas Instruments Literature No. SCBA017, SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <a href="https://www.ti.com">https://www.ti.com</a>.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.



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